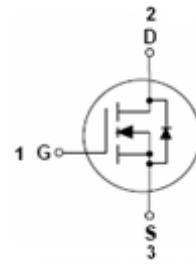


### Features

- Low power loss by high speed switching and low on-resistance
- Ultra-fast body diode
- Excellent thermal behavior
- Product validation acc. JEDEC Standard
- HBM: JESD22-A114-B: 1C
- RoHS compliant with Halogen-free

HF

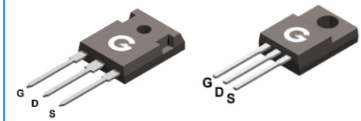


### Applications

- Soft switching applications
- DC-DC converters
- On-Board battery Chargers
- LED lighting

### Mechanical Data

- Case: TO-247, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



TO-247

ITO-220AB

### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SJ65R099FRU	TO-247	30 pcs / Tube	SJ65R099FRU
SJ65R099FRF	ITO-220AB	50 pcs / Tube	SJ65R099FRF

### Maximum Ratings (@ T<sub>C</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	650	V
Gate-to-Source Voltage	V <sub>GSS</sub>	±30	V
Continuous Drain Current (T <sub>C</sub> = 25°C)	I <sub>D</sub>	35	A
Continuous Drain Current (T <sub>C</sub> = 100°C)		22	
Pulsed Drain Current (t <sub>p</sub> = 10μs, T <sub>C</sub> = 25°C)	I <sub>DM</sub>	140	A
Single Pulse Avalanche Energy <sup>2</sup>	E <sub>AS</sub>	800	mJ
Power Dissipation (TO-247, T <sub>C</sub> = 25°C)	P <sub>D</sub>	208	W
Power Dissipation (ITO-220AB, T <sub>C</sub> = 25°C)		42	
Operating Junction Temperature Range	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C

### Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case (TO-247)	R <sub>θJC</sub>	-	0.35	0.6	°C/W
Thermal Resistance Junction-to-Case (ITO-220AB)		-	1.9	3	°C/W
Thermal Resistance Junction-to-Air (TO-247)	R <sub>θJA</sub>	-	-	40	°C/W
Thermal Resistance Junction-to-Air (ITO-220AB)		-	-	62	°C/W

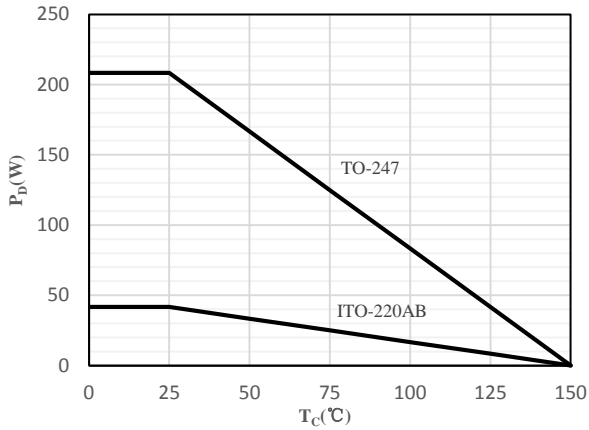
### Electrical Characteristics (@ T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
V <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	650	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650V, V <sub>GS</sub> = 0V	-	-	10	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V	-	-	±100	nA
<b>On Characteristics</b>						
R <sub>DS(ON)</sub>	Drain-Source On-resistance *1	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	-	80	99	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5	3.7	4.5	V
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 0V, f = 1MHz	-	1.9	-	Ω
<b>Dynamic Characteristics</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 40V f = 250kHz	-	2270	-	pF
C <sub>OSS</sub>	Output Capacitance		-	196	-	
C <sub>RSS</sub>	Reverse Transfer Capacitance		-	6.7	-	
<b>Switching Characteristics</b>						
t <sub>d(ON)</sub>	Turn-on Delay Time*3	V <sub>DD</sub> = 400V V <sub>GS</sub> = 10V I <sub>D</sub> = 20A R <sub>G</sub> = 10Ω	-	65	-	ns
t <sub>r</sub>	Turn-on Rise Time*3		-	5.5	-	
t <sub>d(OFF)</sub>	Turn-Off Delay Time*3		-	121	-	
t <sub>f</sub>	Turn-Off Fall Time*3		-	4.3	-	
Q <sub>G</sub>	Total Gate-Charge	V <sub>DD</sub> = 400V V <sub>GS</sub> = 10V I <sub>D</sub> = 20A	-	77.5	-	nC
Q <sub>GS</sub>	Gate to Source Charge		-	24.3	-	
Q <sub>GD</sub>	Gate to Drain (Miller) Charge		-	34.5	-	
<b>Source-Drain Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage *1	I <sub>SD</sub> = 20A, V <sub>GS</sub> = 0V	-	0.9	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 20A, V <sub>R</sub> = 400V	-	170	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt = 100A/μs	-	1.1	-	μC

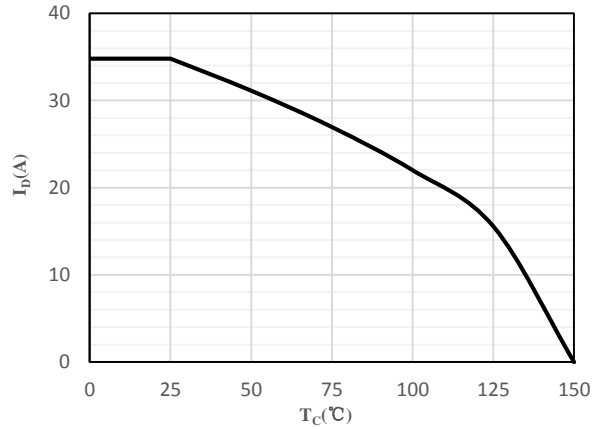
Notes:

- The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
- The E<sub>AS</sub> data shows Max. rating. The test condition is V<sub>DD</sub> = 100V, V<sub>GS</sub> = 15V, L = 50mH
- Guaranteed by design, not subject to production

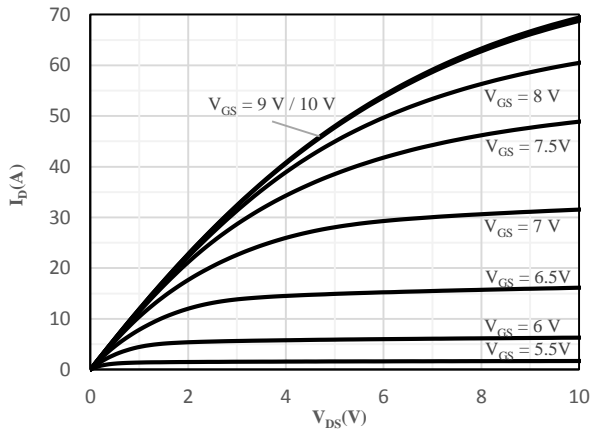
**Ratings and Characteristics Curves** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)



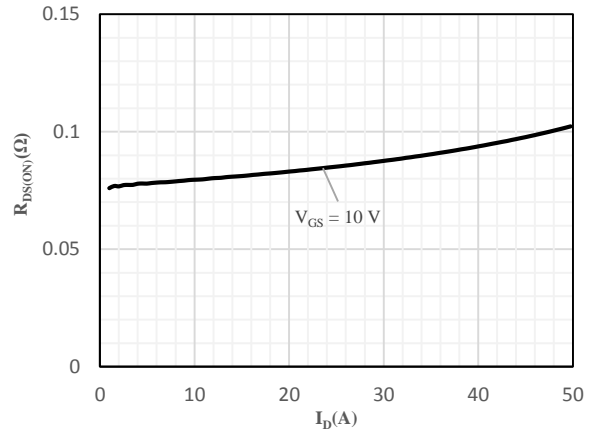
**Fig 1 Power Dissipation**



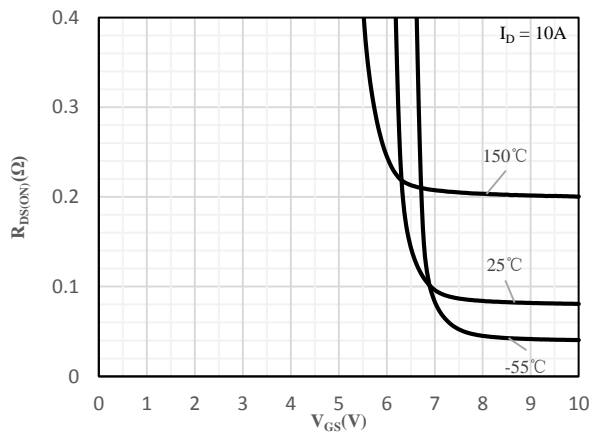
**Fig 2 Drain Current**



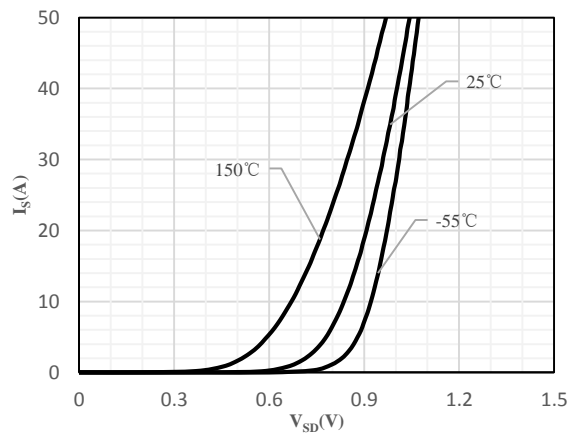
**Fig 3 Typical Output Characteristics**



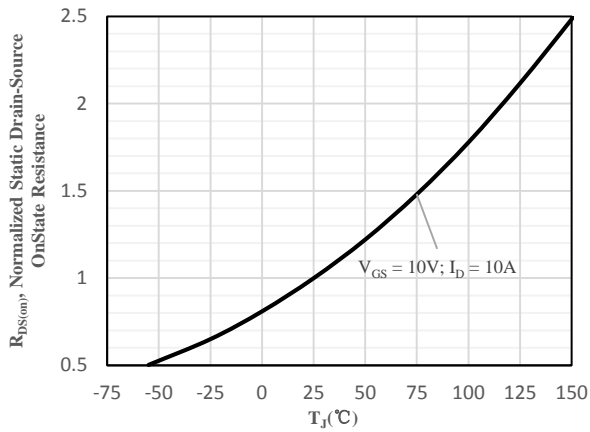
**Fig 4 On-Resistance vs. Drain Current and Gate Voltage**



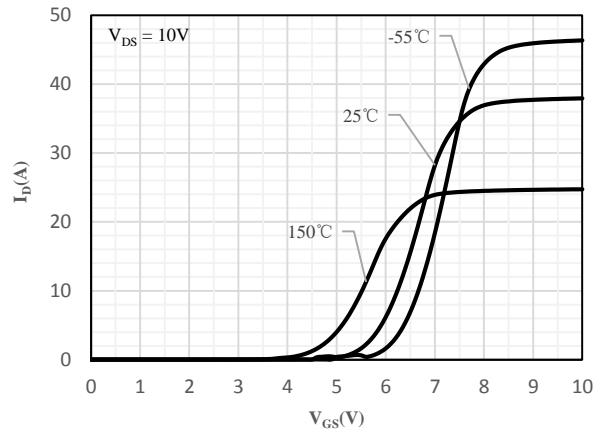
**Fig 5 On-Resistance vs. Gate-Source Voltage**



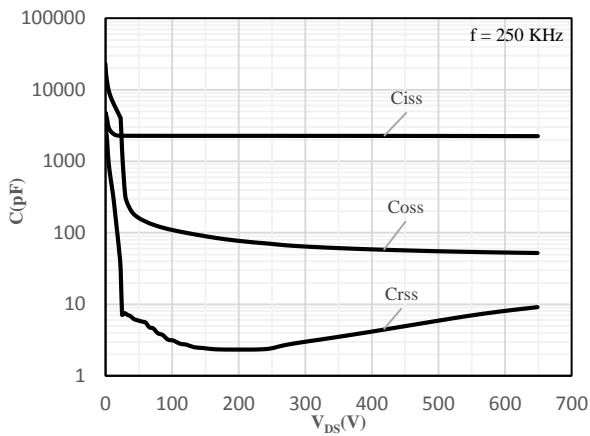
**Fig 6 Body-Diode Characteristics**



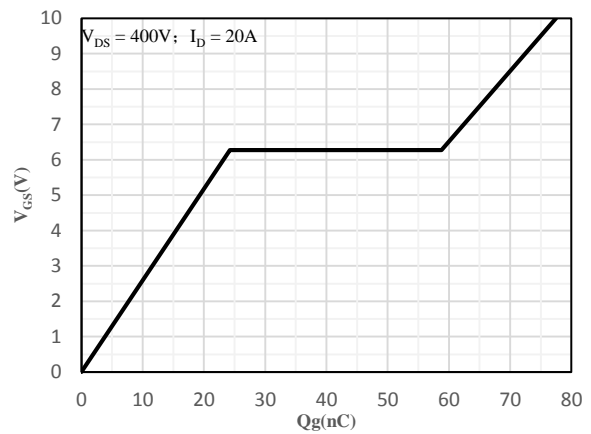
**Fig 7 Normalized On-Resistance vs. Junction Temperature**



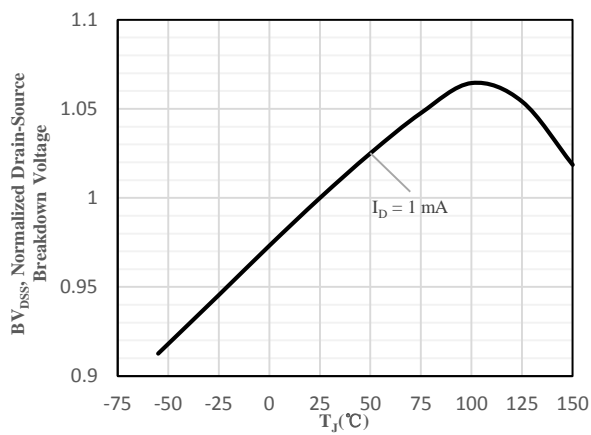
**Fig 8 Transfer Characteristics**



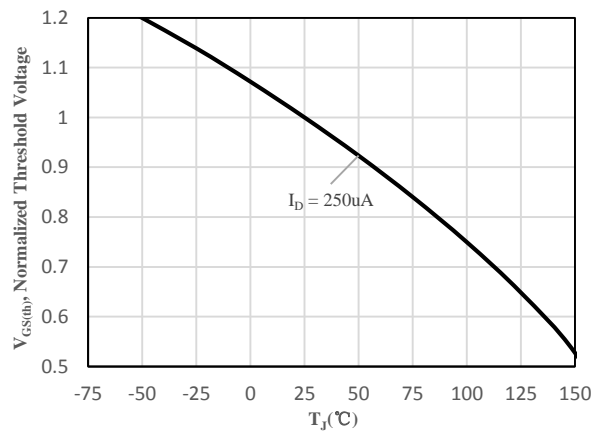
**Fig 9 Capacitance Characteristics**



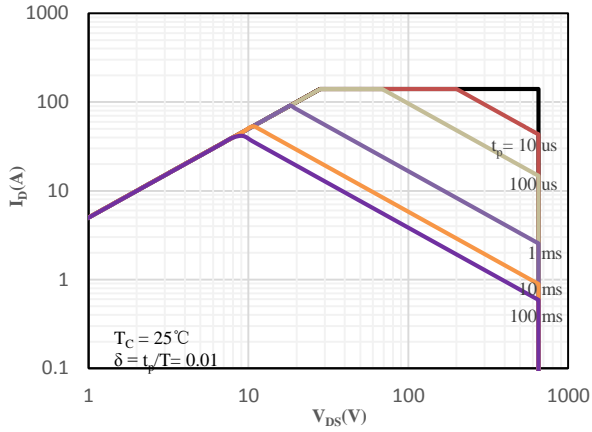
**Fig 10 Gate-Charge Characteristics**



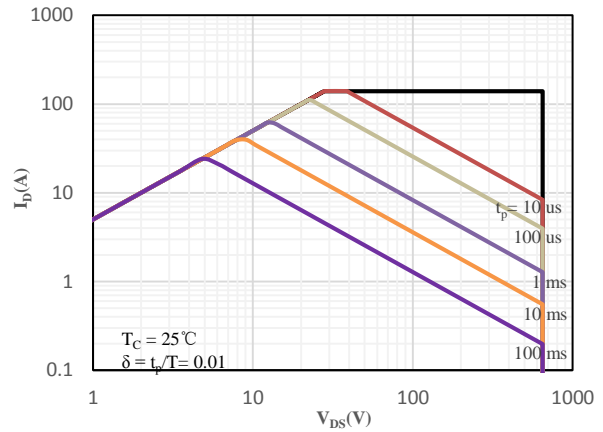
**Fig 11 Normalized Breakdown Voltage vs. Junction Temperature**



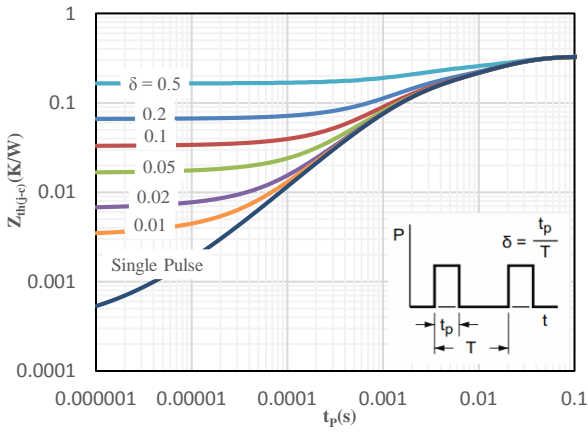
**Fig 12 Normalized  $V_{GS(th)}$  vs. Junction Temperature**



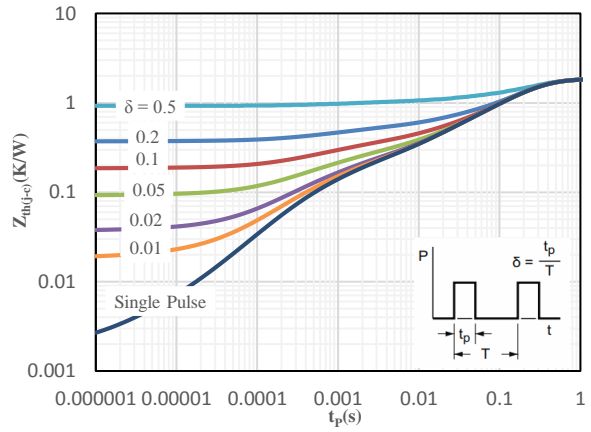
**Fig 13 Safe Operating Area (TO-247)**



**Fig 14 Safe Operating Area (ITO-220AB)**



**Fig 15 Maximum transient thermal impedance (TO-247)**



**Fig 16 Maximum transient thermal impedance (ITO-220AB)**

### Package Outline Dimensions (Unit: mm)

